

Figure 1: Sulfur to tantalum ratio as function of the  $H_2$  flow ratio. The total  $H_2 + H_2S$  flow is 10 sccm. No addition of  $H_2$  leads to a TaS<sub>3</sub> film, while a 50%  $H_2$  flow ratio leads to a TaS<sub>2</sub> film.



Figure 2: X-ray diffraction spectra of 0%  $H_2$  flow ratio (TaS<sub>3</sub>) and 50%  $H_2$  flow ratio (TaS<sub>2</sub>), indicating that first is amorphous and latter is crystalline. The peak at 56° originates from the Si substrate.



Figure 3: Cumulative probability plot for the time-to-breakdown resulting from time-dependent dielectric breakdown measurements of samples without barrier, with amorphous TaS<sub>3</sub> barrier and with crystalline TaS<sub>2</sub> barrier. The mean time-to-failure ( $TTF_{50\%}$ ) is used as a quantitative measure for the barrier performance.